



STB34NM60ND, STF34NM60ND STP34NM60ND, STW34NM60ND

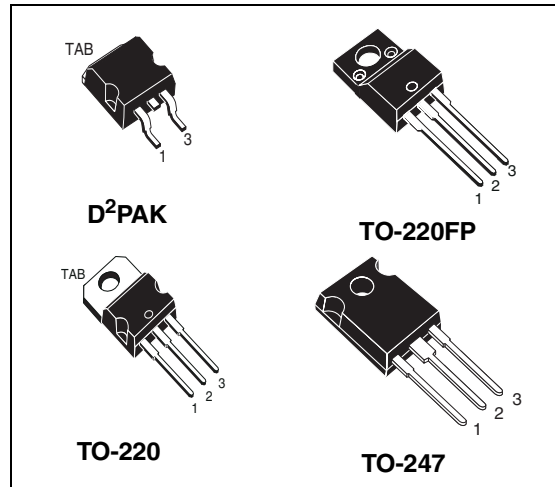
N-channel 600 V, 0.097 Ω , 29 A FDmesh™ II Power MOSFET
(with fast diode) D²PAK, TO-220FP, TO-220, TO-247

Preliminary data

Features

Order codes	V _{DSS} @T _J max.	R _{DS(on)} max.	I _D
STB34NM60ND STF34NM60ND STP34NM60ND STW34NM60ND	650 V	0.110 Ω	29 A

- The world's best R_{DS(on)} in TO-220 amongst the fast recovery diode devices
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- Extremely high dv/dt and avalanche capabilities



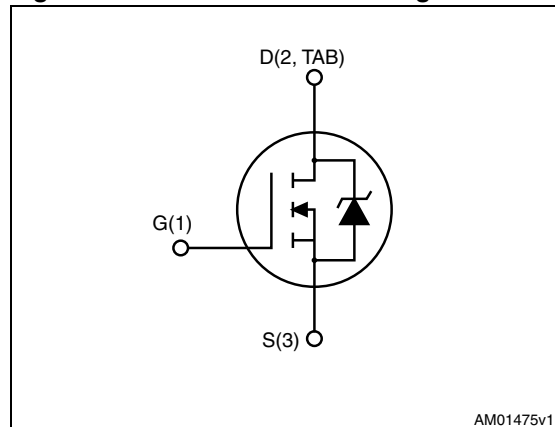
Applications

- Switching applications

Description

These FDmesh™ II Power MOSFETs with intrinsic fast-recovery body diode are produced using the second generation of MDmesh™ technology. Utilizing a new strip-layout vertical structure, these revolutionary devices feature extremely low on-resistance and superior switching performance. They are ideal for bridge topologies and ZVS phase-shift converters.

Figure 1. Internal schematic diagram



AM01475v1

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB34NM60ND	34NM60ND	D ² PAK	Tape and reel
STF34NM60ND	34NM60ND	TO-220FP	Tube
STP34NM60ND	34NM60ND	TO-220	Tube
STW34NM60ND	34NM60ND	TO-247	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		D ² PAK, TO-220, TO-247	TO-220FP	
V _{DS}	Drain-source voltage (V _{GS} = 0)	600		V
V _{GS}	Gate- source voltage	± 25		V
I _D	Drain current (continuous) at T _C = 25 °C	29	29 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	18	18 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	116	116 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	190	40	W
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T _C =25 °C)	2500		V
dv/dt ⁽³⁾	Peak diode recovery voltage slope	15		V/ns
T _{stg}	Storage temperature	- 55 to 150		°C
T _J	Max. operating junction temperature	150		

1. Current limited by package
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 29 \text{ A}$, $di/dt \leq 600 \text{ A}/\mu\text{s}$, $V_{DD} = 80\% V_{(BR)DSS}$, $V_{Peak} < V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	TO-220	TO-247	D ² PAK	TO-220FP	Unit
R _{thj-case}	Thermal resistance junction-case max	0.66			3.1	°C/W
R _{thj-amb}	Thermal resistance junction-ambient max	62.5	50		62.5	°C/W
R _{thj-pcb}	Thermal resistance junction-pcb max			30		°C/W

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _J max)	7	A
E _{AS}	Single pulse avalanche energy (starting T _J = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	345	mJ

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 600\text{ V}$ $V_{DS} = 600\text{ V}, T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}, I_D = 14.5\text{ A}$		0.097	0.110	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	2785	-	pF
C_{oss}	Output capacitance			168		pF
C_{rss}	Reverse transfer capacitance			5		pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0\text{ to }480\text{ V}$	-	43.8	-	pF
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}, I_D = 14.5\text{ A}$ $R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$ (see Figure 18 and 23)	-	30	-	ns
t_r	Rise time			53.4		ns
$t_{d(off)}$	Turn-off delay time			111		ns
t_f	Fall time			61.8		ns
Q_g	Total gate charge	$V_{DD} = 480\text{ V}, I_D = 29\text{ A},$ $V_{GS} = 10\text{ V},$ (see Figure 19)	-	80.4	-	nC
Q_{gs}	Gate-source charge			16		nC
Q_{gd}	Gate-drain charge			41.4		nC
R_g	Gate input resistance	$f = 1\text{ MHz}, \text{ open drain}$	-	2.87	-	Ω

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		29	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		116	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 29\text{ A}, V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 29\text{ A}, V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ (see Figure 20)	-	175		ns
Q_{rr}	Reverse recovery charge			1.4		μC
I_{RRM}	Reverse recovery current			16		A
t_{rr}	Reverse recovery time	$I_{SD} = 29\text{ A}, V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 20)	-	255		ns
Q_{rr}	Reverse recovery charge			2.6		μC
I_{RRM}	Reverse recovery current			20		A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220FP

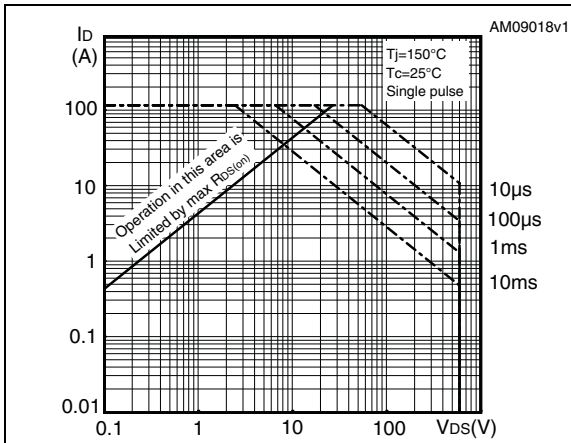


Figure 3. Thermal impedance for TO-220FP

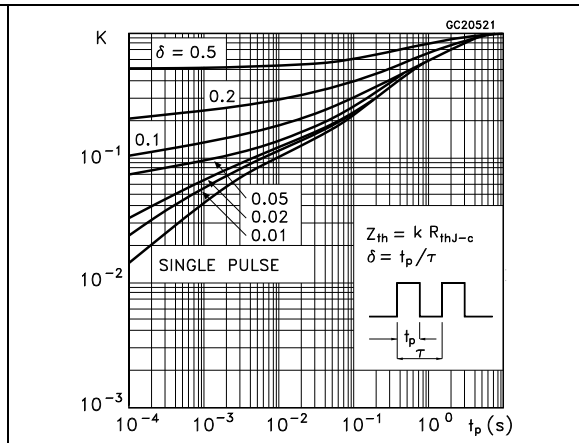


Figure 4. Safe operating area for TO-220 and D²PAK

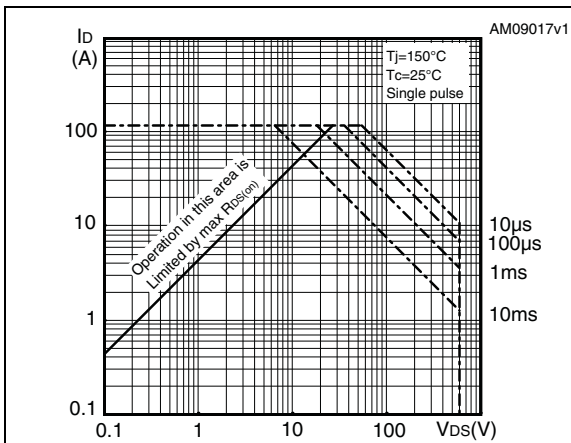


Figure 5. Thermal impedance for TO-220 and D²PAK

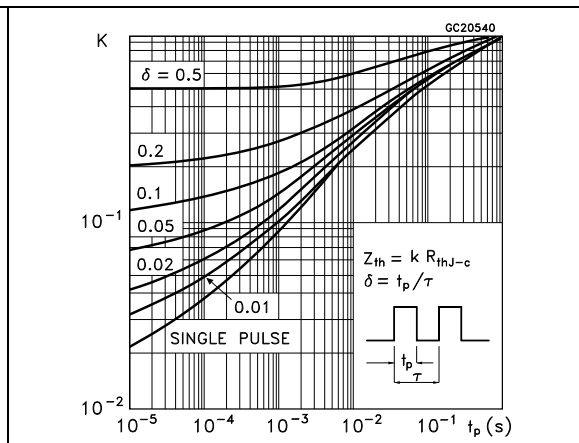


Figure 6. Safe operating area for TO-247

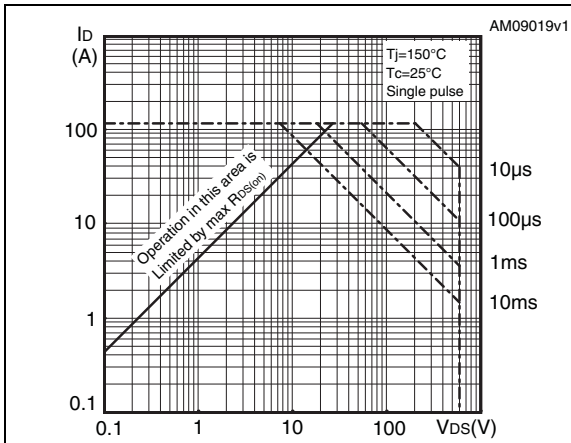


Figure 7. Thermal impedance for TO-247

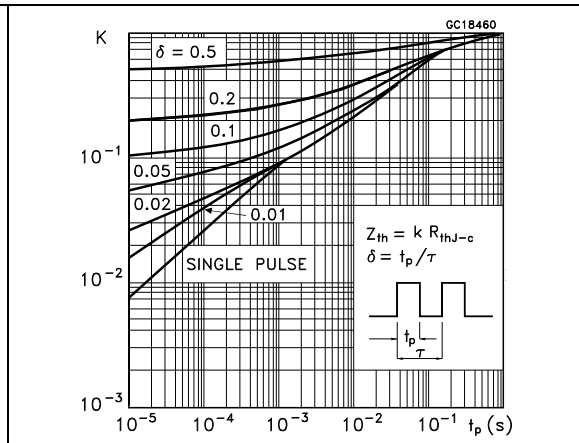


Figure 8. Output characteristics

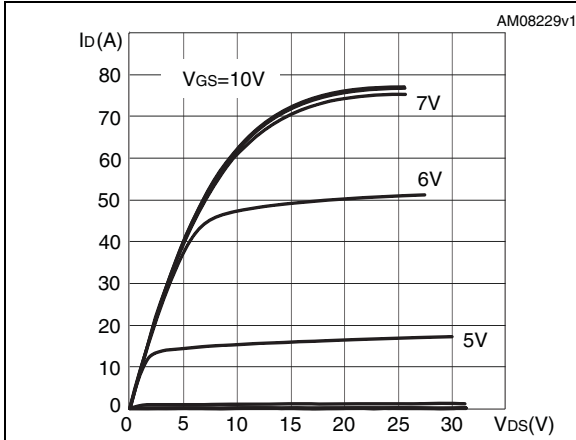


Figure 9. Transfer characteristics

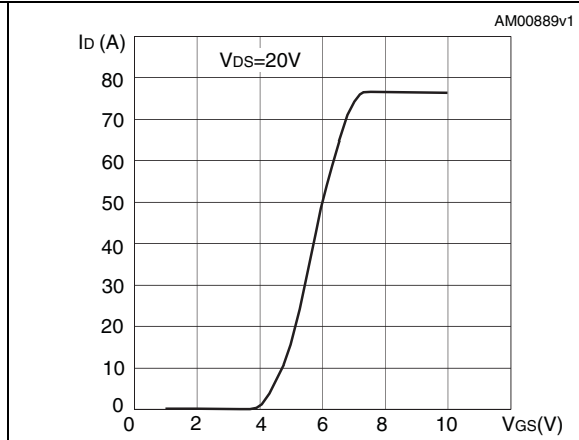


Figure 10. Gate charge vs gate-source voltage

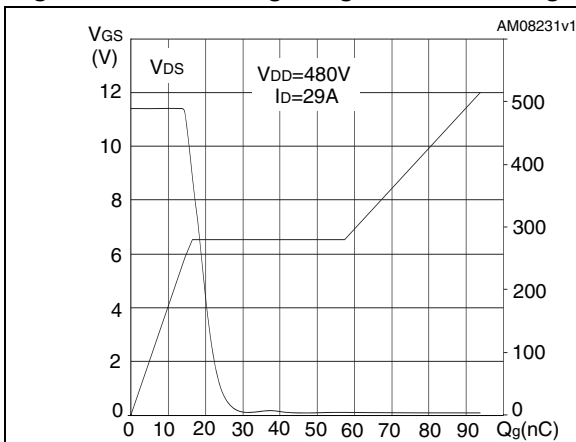


Figure 11. Static drain-source on resistance

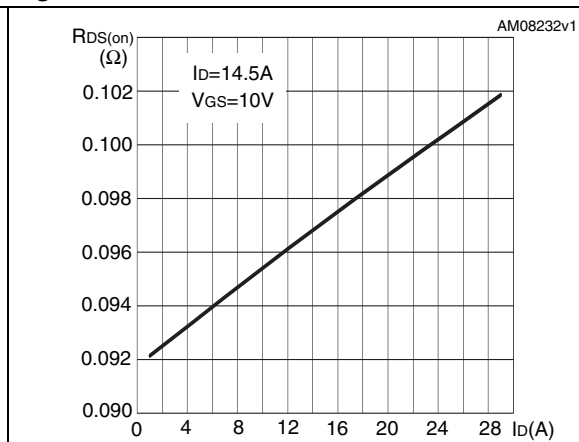


Figure 12. Capacitance variations

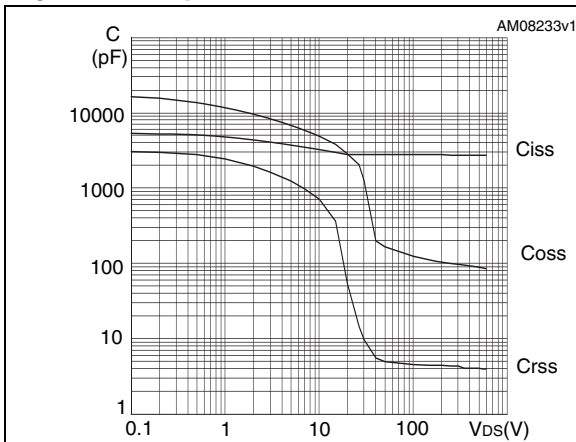


Figure 13. Output capacitance stored energy

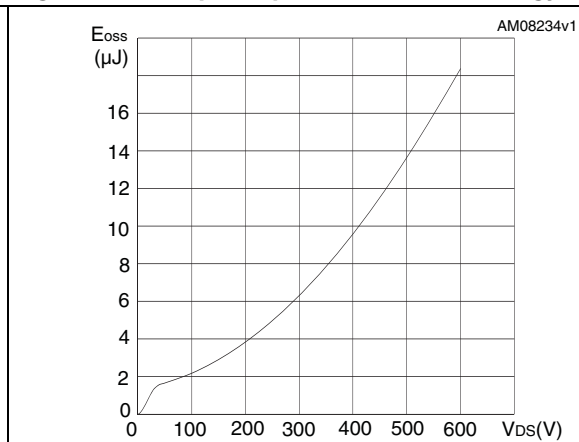


Figure 14. Normalized gate threshold voltage vs temperature

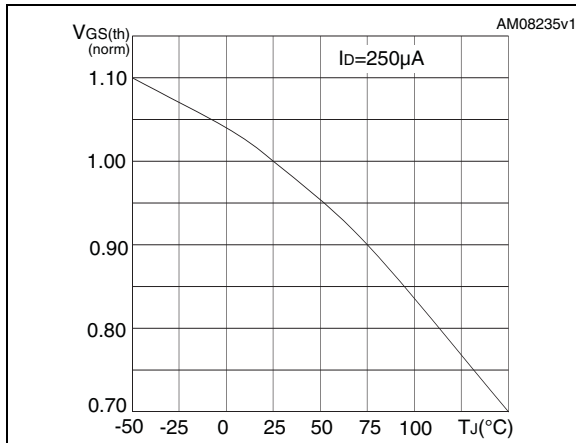


Figure 15. Normalized on resistance vs temperature

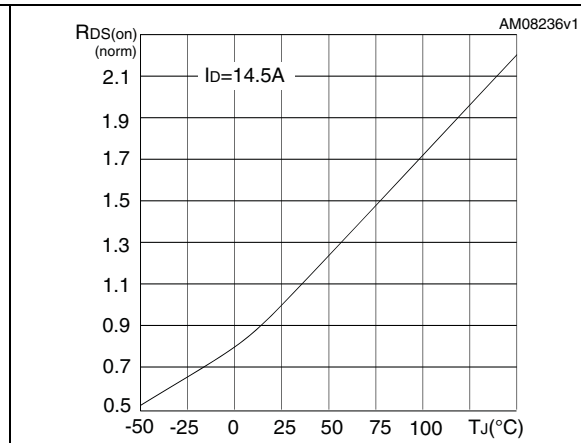


Figure 16. Normalized B_VDSS vs temperature

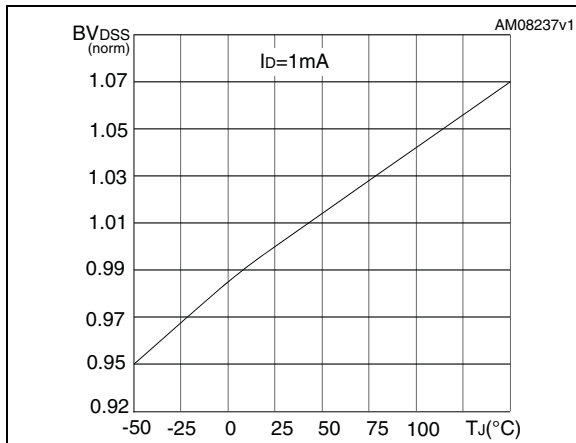
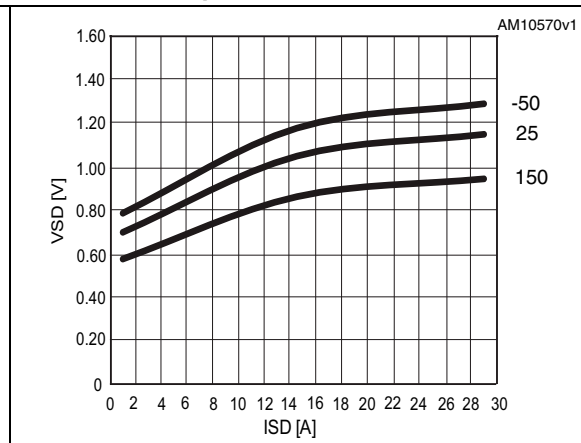


Figure 17. Source-drain diode forward vs temperature



3 Test circuits

Figure 18. Switching times test circuit for resistive load

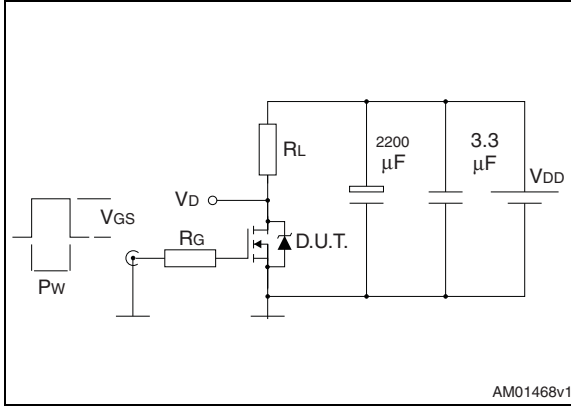


Figure 19. Gate charge test circuit

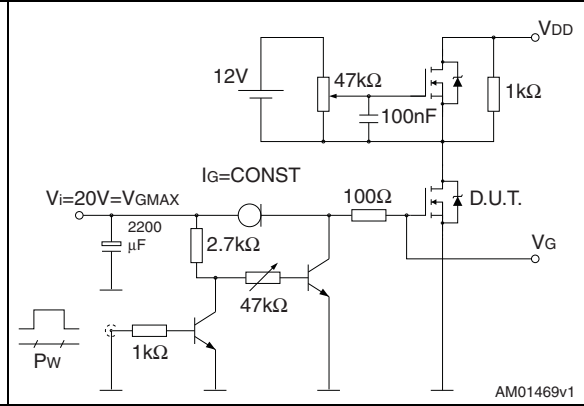


Figure 20. Test circuit for inductive load switching and diode recovery times

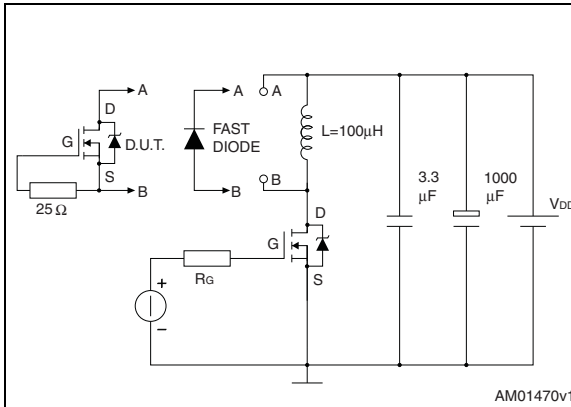


Figure 21. Unclamped inductive load test circuit

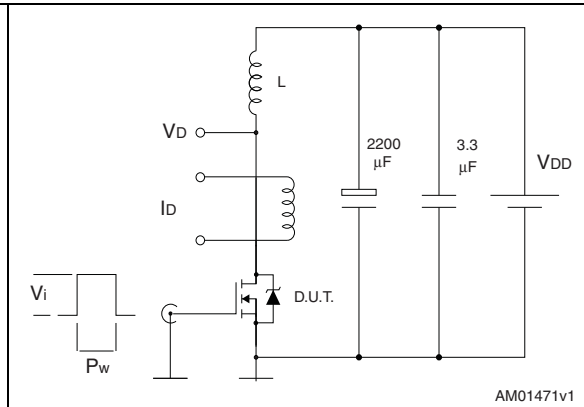


Figure 22. Unclamped inductive waveform

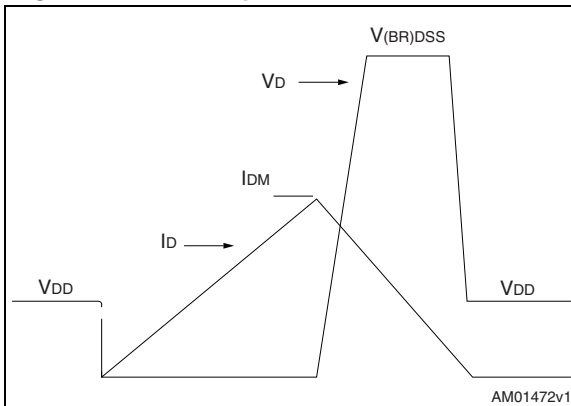
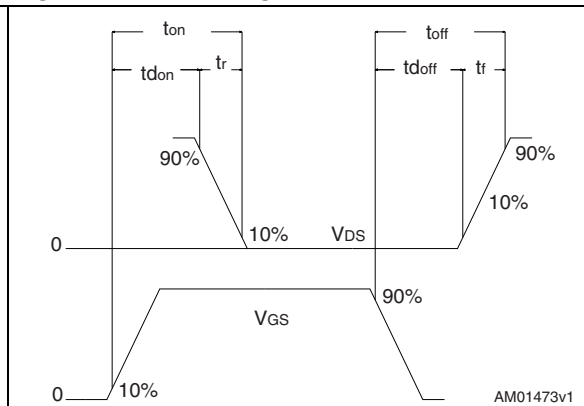


Figure 23. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 8. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 24. D²PAK (TO-263) drawing

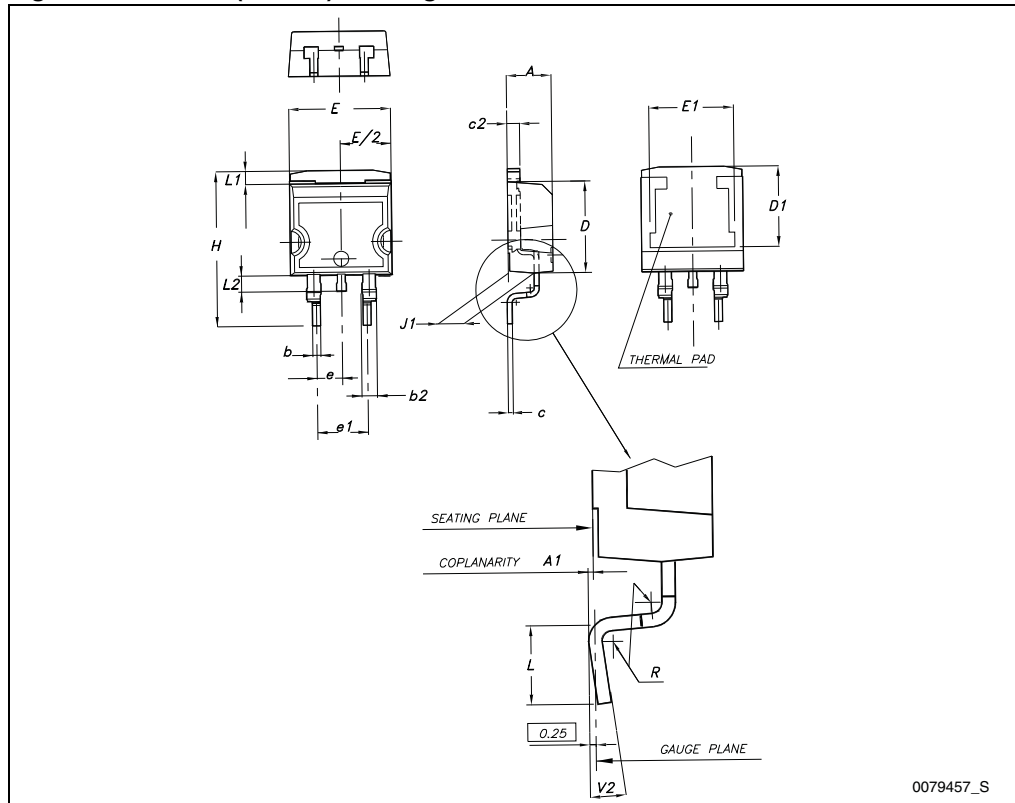
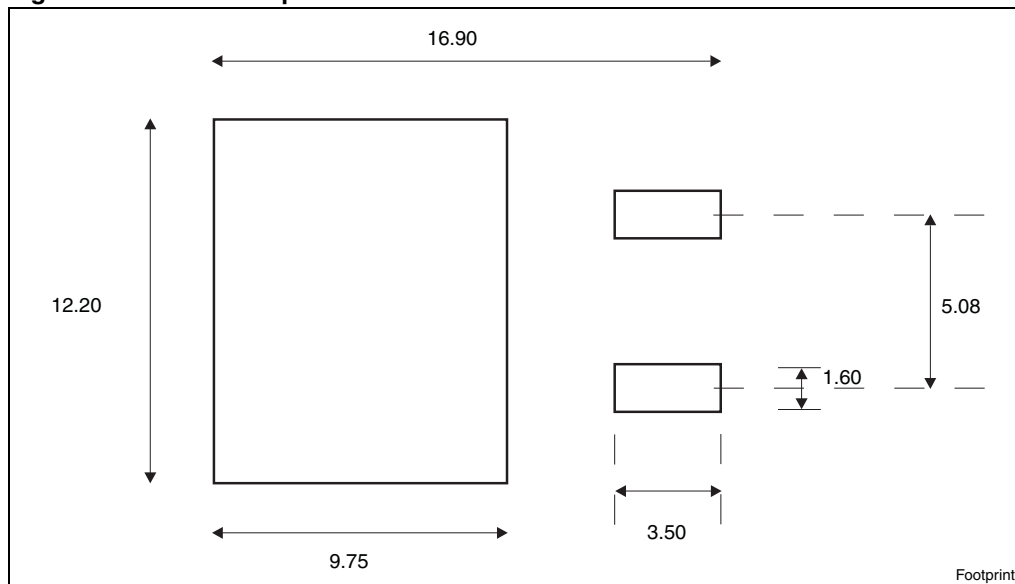


Figure 25. D²PAK footprint^(a)



a. All dimension are in millimeters

Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 26. TO-220FP drawing

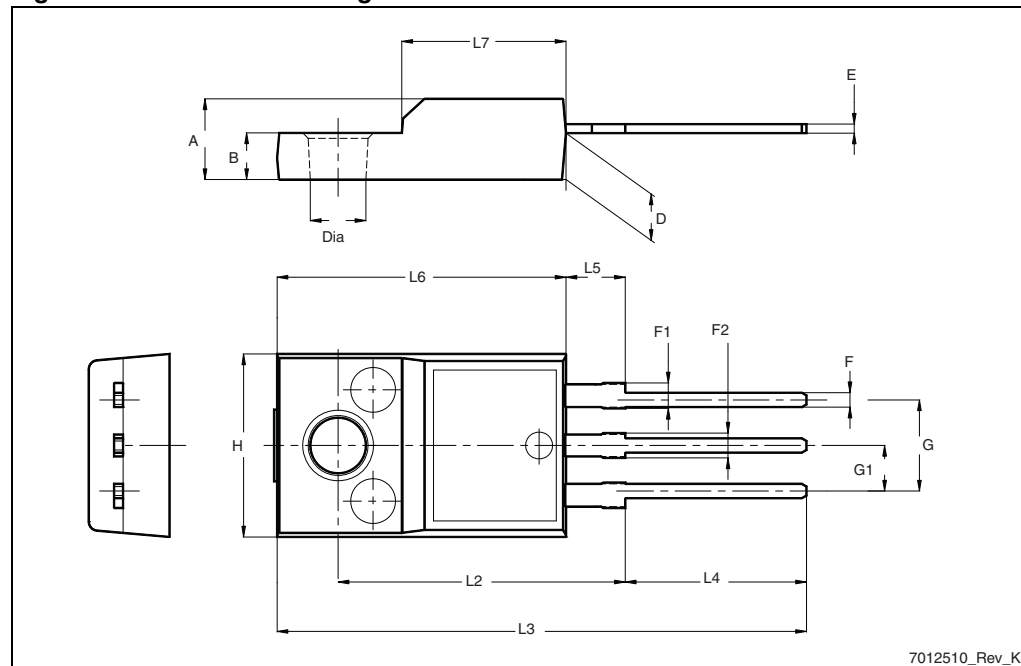


Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 27. TO-220 type A drawing

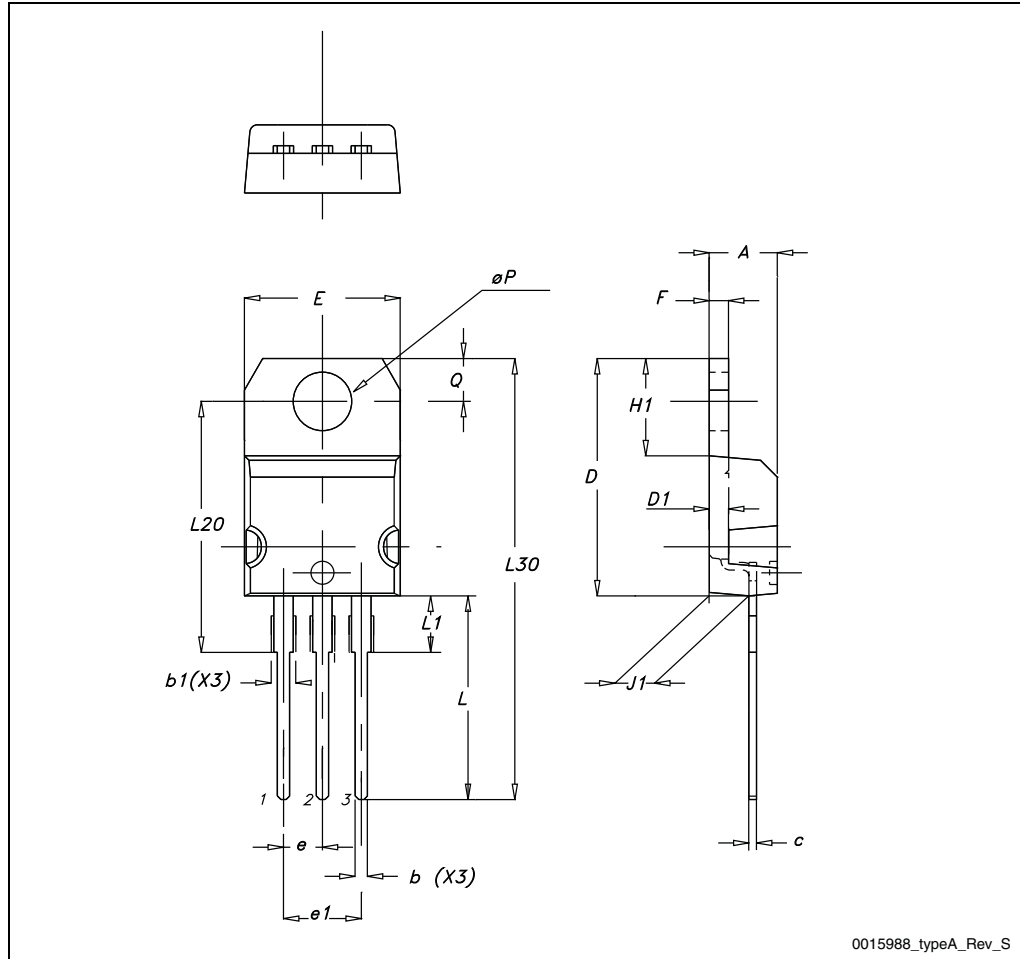
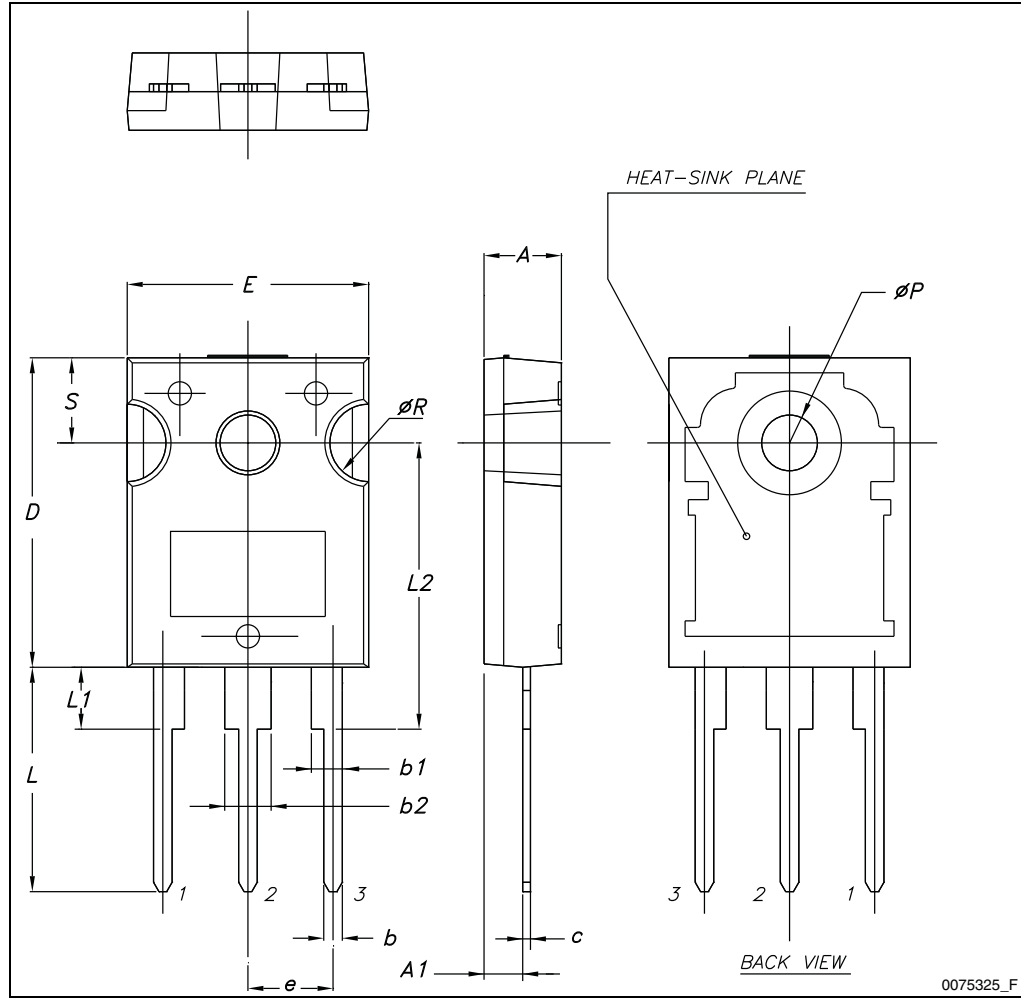


Table 11. TO-247 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S		5.50	

Figure 28. TO-247 drawing



5 Packaging mechanical data

Table 12. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 29. Tape

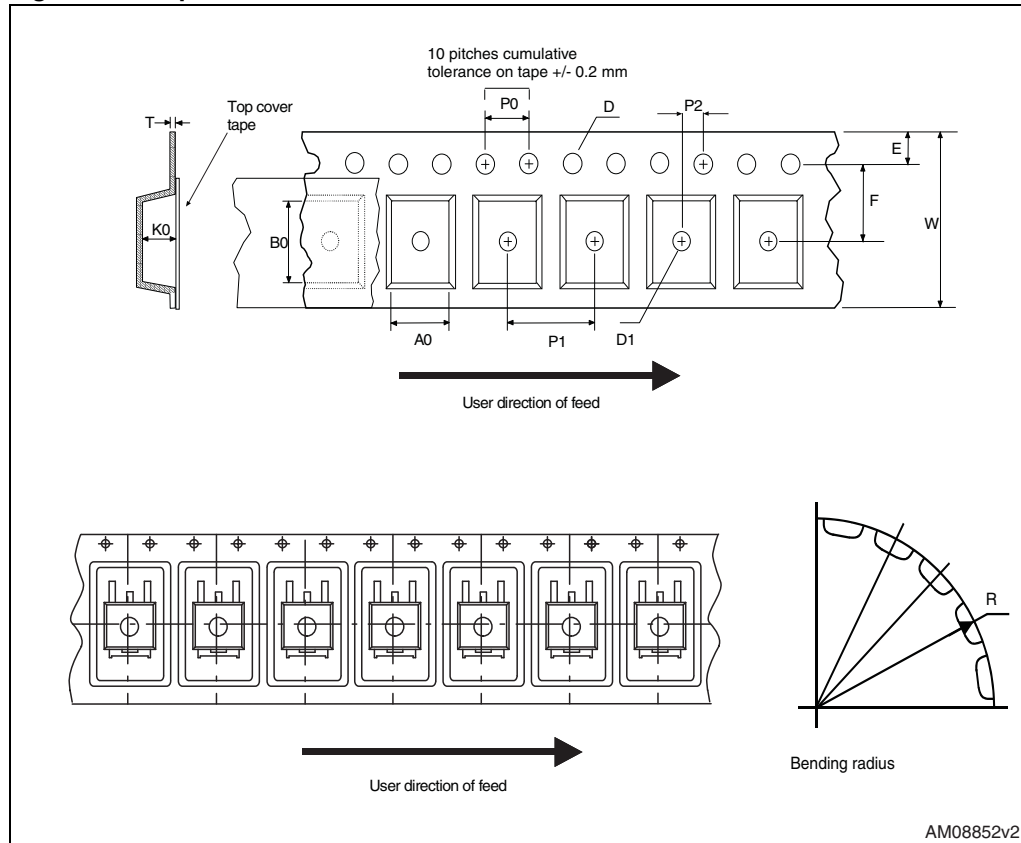
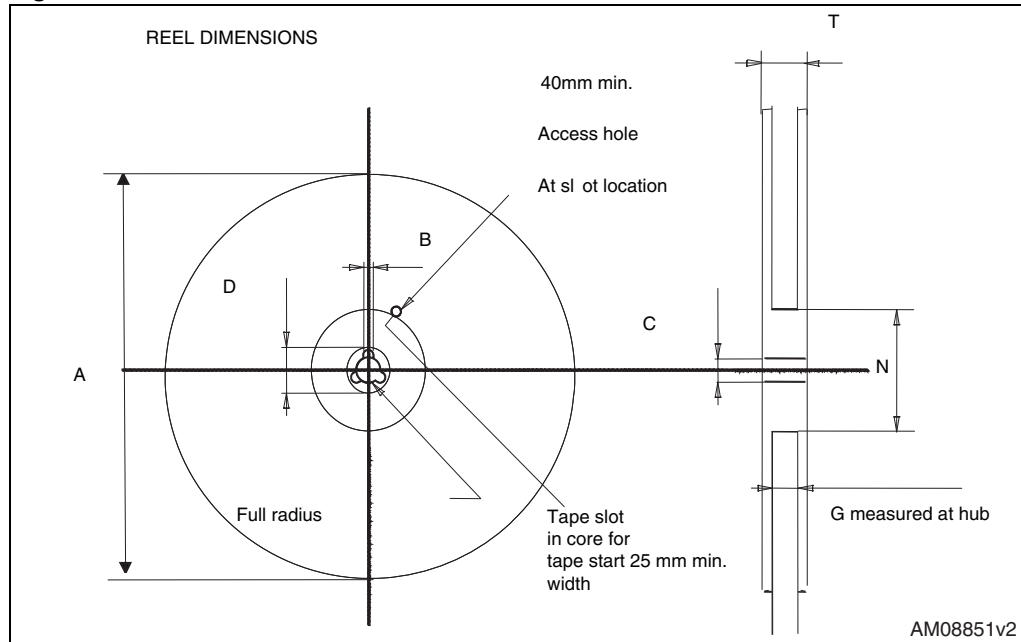


Figure 30. Reel



6 Revision history

Table 13. Document revision history

Date	Revision	Changes
04-Nov-2010	1	Initial release.
18-Apr-2011	2	Corrected E_{AS} value in Table 4: Avalanche characteristics
14-Sep-2011	3	Added order code in D ² PAK and TO-220FP Updated Table 1: Device summary , Table 2: Absolute maximum ratings and Table 3: Thermal data . Updated Section 4: Package mechanical data . Added Section 5: Packaging mechanical data . Minor text changes.
29-Dec-2011	4	Updated description in cover page.

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